

FK8V03060L Datasheet



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DiGi Electronics Part Number FK8V03060L-DG

Manufacturer Panasonic Electronic Components

Manufacturer Product Number FK8V03060L

Description MOSFET N CH 33V 6.5A WMINI8

Detailed Description N-Channel 33 V 6.5A (Ta) 1W (Ta) Surface Mount W

Mini8-F1



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RFQ Email: Info@DiGi-Electronics.com



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FK8V03060L	Panasonic Electronic Components
Series:	Product Status:
	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
33 V	6.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	20m0hm @ 3.3A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 0.48mA	3.8 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	360 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	1W (Ta)
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
WMini8-F1	8-SMD, Flat Lead

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS Compliant	1 (Unlimited)
ECCN:	HTSUS:
EAR99	8541.29.0095

Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

MOS FET

FK8V03060L

FK8V03060L

Silicon N-channel MOS FET

For lithium-ion secondary battery protection circuit For DC-DC Converter

■ Features

- Low drain-source On-state Resistance RDS(on) typ. = 22 m Ω (VGS = 4.5 V)
- High-speed switching : Qg = 3.8 nC
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 3F

■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter Symbol Rating Unit

Drain-source Voltage VDS 33 V

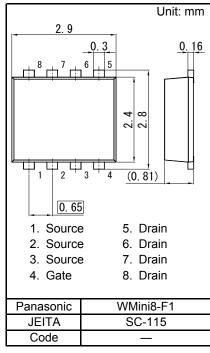
Gate-source Voltage VGS ±20 V

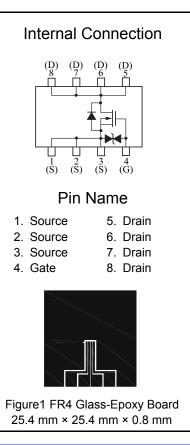
Drain Current (Steady State) *1 ID 6.5

Gate-source Voltage	VGS	±20	V	
Drain Current (Steady State) *1	ID	6.5		
Drain Current (t = 10 s) *1	טו	8		
Drain Current (Pulsed) *1,*2	IDp	26	Α	
Source Current (Pulsed)	ISp	6.5		
(Body Diode) *1,*2	(BD)	0.5		
Total Power Dissipation (Steady State) *1	PD	1	W	
Total Power Dissipation (t = 10 s) *1	רט	1.5	VV	
Channel Temperature	Tch	150	°C	
Operating Ambient Temperature	Topr	-40 to +85	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	

Note) *1 Device mounted on a glass-epoxy board (See Figure 1)

*2 Pulse test: Ensure that the channel temperature does not exceed 150°C





MOS FET

FK8V03060L

■ Electrical Characteristics Ta = 25°C ± 3°C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	1		2.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = 3.3 A, VGS = 10 V		15	20	m()
Drain-source On-state Resistance	RDS(on)2	ID = 3.3 A. VGS = 4.5 V		22	35	mΩ

Dynamic Characteristics

Input Capacitance	Ciss	VDC = 40.V VCC = 0.V	360	
Output Capacitance	Coss	VDS = 10 V, VGS = 0 V f = 1 MHz	70	pF
Reverse Transfer Capacitance	Crss	1 - 1 1011 12	50	
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V	8	
Rise Time *2	tr	ID = 3.3 A	3	ns
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V	24	115
Fall Time *2	tf	ID = 3.3 A	9	
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V,	3.8	
Gate-source Charge	Qgs	ID = 6.5 A	1.4	nC
Gate-drain Charge	Qgd	ID = 0.5 A	1.6	

Body	Diode	Characte	ristic

Diode Forward Voltage *1	VSD	IS = 3.3 A, VGS = 0 V	8.0	1.2	V
				_	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

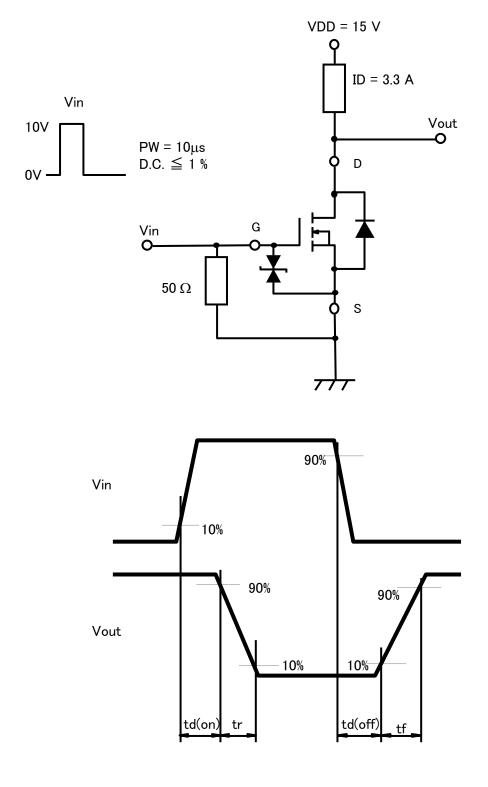
Establ shied: 2 0-01-61 Revised: 2 0-01-83

^{2. *1} Pulse test: Ensure that the channel temperature does not exceed 150°C

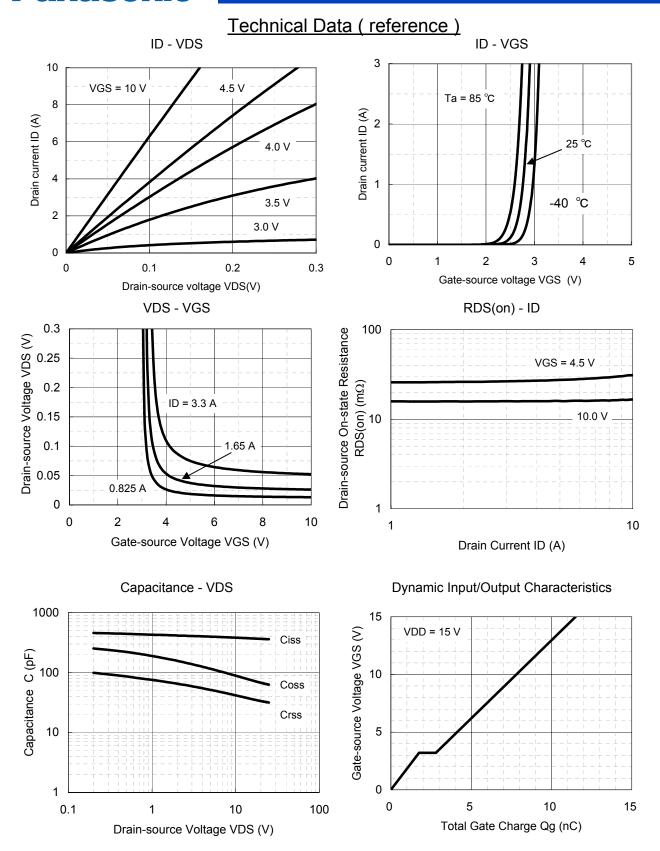
^{*2} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

MOS FET FK8V03060L

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



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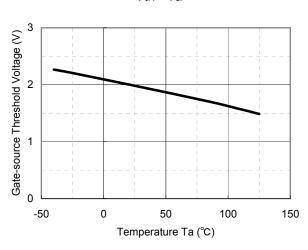


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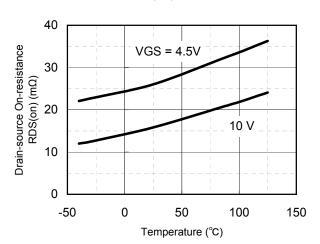
MOS FET FK8V03060L

Technical Data (reference)

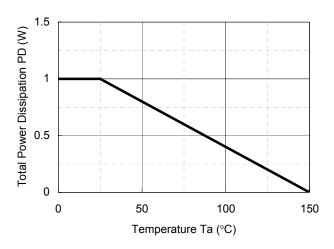
Vth - Ta



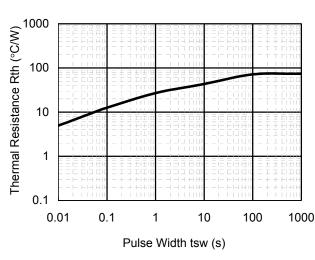
RDS(on) - Ta



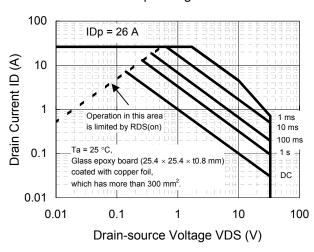
PD - Ta



Rth - tsw



Safe Operating Area

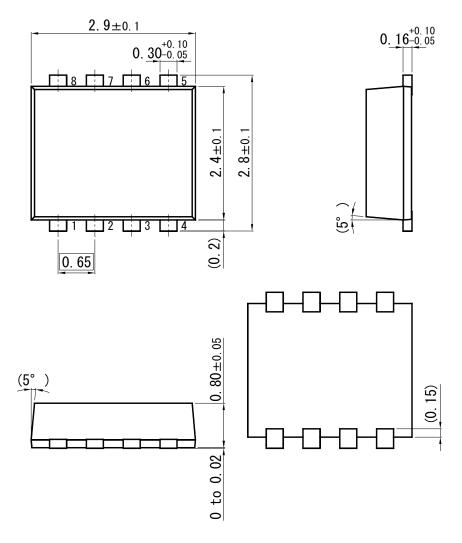


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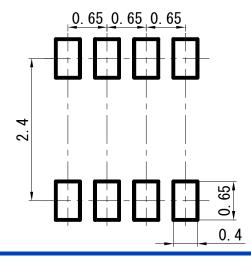
MOS FET FK8V03060L

WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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